L Number	Hits		DB	Time stamp
1	360	438/471	USPAT	2004/04/14 10:52
2	171	438/474	USPAT	2004/04/14 10:52
3	157	438/475	USPAT	2004/04/14 10:52
4	983	438/680	USPAT	2004/04/14 10:52
5	472	438/681	USPAT	2004/04/14 10:52
6	1448	438/687	USPAT	2004/04/14 10:53
7	160	438/679	USPAT	2004/04/14 10:53
8	1073	438/675	USPAT	2004/04/14 10:53
9	1442	438/706	USPAT	2004/04/14 10:53
10	1235	438/700	USPAT	2004/04/14 10:53
11	404	438/715	USPAT	2004/04/14 10:53
12	143	438/732	USPAT	2004/04/14 10:53
13	213	438/733	USPAT	2004/04/14 10:53
14	489	438/740	USPAT	2004/04/14 10:53
15	318	438/905	USPAT	2004/04/14 10:53
16	570	438/906	USPAT	2004/04/14 10:54
10	3/0	10/636168	USPAT	2004/04/14 09:15
•				
-	1	("6126806").PN.	USPAT	2004/04/14 09:15
-	1	("6235406").PN.	USPAT	2004/04/14 09:15
•	1	("6355571").PN.	USPAT	2004/04/14 09:16
-	0	(dual adj damascene) and trench and CMP and (annealing adj	USPAT	2004/04/14 09:18
		process) and in-situ and cooling and chamber and hydrogen		
		and cleaning		
-	0	(dual adj damascene) and trench and CMP and in-situ and	USPAT	2004/04/14 09:19
		cooling and chamber and hydrogen and cleaning and		
		heating		
-	3	(dual adj damascene) and trench and CMP and in-situ and	USPAT	2004/04/14 10:52
		cooling and chamber and hydrogen and cleaning		
-	1		USPAT	2004/04/14 09:21
-	1		USPAT	2004/04/14 09:21
	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	i		USPAT	2004/04/14 09:23
	i		USPAT	2004/04/14 09:24
-	i		USPAT	2004/04/14 09:24
-	i		USPAT	2004/04/14 09:24
_	i		USPAT	2004/04/14 09:21
	i		USPAT	2004/04/14 09:25
	i		USPAT	2004/04/14 09:21
	i		USPAT	2004/04/14 09:2!
	i		USPAT	2004/04/14 09:26
•	i		USPAT	2004/04/14 09:26
•				
-	1	(#E0.7E7.(7#) PM	USPAT	2004/04/14 09:26
-	1	("5935767").PN.	USPAT	2004/04/14 09:27
•	1	("6380096").PN.	USPAT	2004/04/14 09:27
•	1	(("5935767").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:36
		hole or opening or via or aperture or cleaning or process or		
		CMP or chamber or reactive or reaction or hydrogen or		
		polymer or in-situ or metal or conductive or insulating or		
		dielectric or side or wall or photo or resist or upper or lower		
		or line or substrate or pattern or single or gas or inert or	ł	
		pressure or power or SIOC or copper or seed or material or	1	
		oxide or remove or removing or burying or impplementing		1
		or cooling opr cool or annealing or heating or temperature)		

•	T .	(("5935762").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:42
	i	hole or opening or via or aperture or cleaning or process or	ļ	
	i	CMP or chamber or reactive or reaction or hydrogen or	!	
	1	polymer or In-situ or metal or conductive or insulating or	ł	
		dielectric or side or wall or photo or resist or upper or lower		
		or line or substrate or pattern or single or gas or inert or		
	ł	pressure or power or SiOC or copper or seed or material or		
	i	oxide or remove or removing or burying or Impplementing		
		or cooling opr cool or annealing or heating or temperature)	!	
	1	(("6380096").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:48
		hole or opening or via or aperture or cleaning or process or		
		CMP or chamber or reactive or reaction or hydrogen or		
1		polymer or In-situ or metal or conductive or insulating or		1
1	ŀ	dielectric or side or wall or photo or resist or upper or lower		
	ŀ	or line or substrate or pattern or single or gas or inert or		t
	i	pressure or power or SIOC or copper or seed or material or		Ī
	İ			
1		oxlde or remove or removing or burying or impplementing		
	١.	or cooling opr cool or annealing or heating or temperature)	LICEAT	0004/04/14 00 40
1-	1	(("6126806").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:49
		hole or opening or via or aperture or cleaning or process or		
		CMP or chamber or reactive or reaction or hydrogen or		
	·	polymer or In-situ or metal or conductive or Insulating or		1
		dielectric or side or wall or photo or resist or upper or lower		
	t	or line or substrate or pattern or single or gas or Inert or		
		pressure or power or SiOC or copper or seed or material or		
		oxide or remove or removing or burying or impplementing		ł .
		or cooling opr cool or annealing or heating or temperature)		
-	1	(("6235406").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:49
		hole or opening or via or aperture or cleaning or process or		
		CMP or chamber or reactive or reaction or hydrogen or		
		polymer or In-situ or metal or conductive or insulating or		
		dielectric or side or wall or photo or resist or upper or lower		•
		or line or substrate or pattern or single or gas or inert or		İ
		pressure or power or SIOC or copper or seed or material or		1
l		oxide or remove or removing or burying or imppiementing		
		or cooling opr cool or annealing or heating or temperature)		
l.	1	(("6355571").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:51
-	'	hole or opening or via or aperture or cleaning or process or	usi Ai	2004/04/14 09:51
		CMP or chamber or reactive or reaction or hydrogen or		
		polymer or in-situ or metal or conductive or insulating or		
		dielectric or side or wall or photo or resist or upper or lower		
1		or line or substrate or pattern or single or gas or linert or		
1	l			
		pressure or power or SiOC or copper or seed or material or		
	l	oxide or remove or removing or burying or impplementing	1	
		or cooling opr cool or annealing or heating or temperature)	LICEAT	2004/04/14 05 5:
-	1	("5529953").PN.	USPAT	2004/04/14 09:51
-	1	(("5529953").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:52
		hole or opening or via or aperture or cleaning or process or		
		CMP or chamber or reactive or reaction or hydrogen or		
		polymer or In-situ or metal or conductive or Insulating or		
	l	dielectric or side or wall or photo or resist or upper or lower		
		or line or substrate or pattern or single or gas or inert or		
1		pressure or power or SiOC or copper or seed or material or	l	
1		oxide or remove or removing or burying or impplementing	l	
		or cooling opr cool or annealing or heating or temperature)		
1-	1	("5614765").PN.	USPAT	2004/04/14 09:52

·	1 (("5614765").PN.) and (dual or damascene or treanch or	USPAT	2004/04/14 09:52
	hole or opening or via or aperture or cleaning or process or		
1	CMP or chamber or reactive or reaction or hydrogen or		
	polymer or in-situ or metal or conductive or insulating or		
i	dielectric or side or wall or photo or resist or upper or lower		
	or line or substrate or pattern or single or gas or inert or		
	pressure or power or SiOC or copper or seed or material or		
	oxide or remove or removing or burying or impplementing		
	or cooling opr cool or annealing or heating or temperature)		

4/14/04